2811

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PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Atsushi YAMAGUCHI et al. Confirmation No. 1202

Serial No. 09/944,186 Group 2811

Filed September 4, 2001 Examiner Shouxiang Hu

NITRIDE BASED SEMICONDUCTOR
LIGHT-EMITTING DEVICE

REPLACEMENT OF REFERENCES OF IDS OF January 3, 2002

Commissioner for Patents

Alexandria, VA 22313-1450

Sir:

A call from the Examiner who has charge of this application advised us that the references cited in the Information Disclosure Statement of January 3, 2002 are missing from the PTO file.

These are replaced herewith. Also attached is a copy of the IDS of that date and the postcard receipt proving its filing.

Respectfully submitted,

YOUNG & THOMPSON

By _____

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June 26, 2003
RJP/bsg

1/3/02

THE STAMP OF THE PATENT OFFICE MAIL HEREON ACKNOWLEDGES THE RECEIPT OF THE BELOW-IDENTIFIED DOCUMENT ON THE DATE INDICATED BY SUCH STAMP.

In re: Atsushi YAMAGUCHI et al.
S.N. 09/944,186 Group 2811

INFORMATION DISCLOSURE STATEMENT WITH PTO FORM 1449 WITH 10 REFERENCES.

RJP/cam

PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Atsushi YAMAGUCHI et al.

Serial No. 09/944,186 GROUP 2811

Filed September 4, 2001 Examiner Unassigned

NITRIDE BASED SEMICONDUCTOR LIGHT-EMITTING DEVICE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents

Washington, D.C. 20231

Sir:

In compliance with Rules 1.97 and 1.98, and in fulfillment of the duty of disclosure under Rule 1.56, the accompanying documents, copies of which are attached to this statement, are made of record on the enclosed sheet.

A concise explanation of the relevance of these items is that these references were discovered during any searches they or their client had made, or that they were considered in the preparation of the application.

Respectfully submitted,

YOUNG & THOMPSON

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January 3, 2002

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT
(Use several sheets if necessary)

37 CFR 1.98(b)

ATTY. DOCKET NO.	SERIAL NO.
PF-2871	09/944,186

APPLICANT
Atsushi YAMAGUCHI et al.

FILING DATE	GROUP
September 4, 2001	2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						

FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

		DOCUMENT NO.	PUBL. DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION YES NO
	AI	A 11-307866	11/99	JP			with English abstract
	AJ	A 11-340580	12/99	JP			with English abstract
	AK						

OTHER DOCUMENTS (Including Author, Title, Date, Relevant Pages, Place of Publication)

	AL	Shuji NAKAMURA, "Current Status and Future Prospects of InGaN-Based Laser Diodes," JSAP International, Jan. 2000, Tokushima, Japan, pp. 5-17.
	AM	Masaru KURAMOTO et al., "Towards a Durable InGaN MQW LD--Room Temperature CW Operation of InGaN MQW Laser," NEC Res. & Develop., V. 41, January 2000, pp. 74-86.
	AN	Shuji NAKAMURA et al., "InGaN/GaN/AlGaN-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices," Jpn. J. Appl. Phys., V. 36, 1997, pp. L1568-L1571.
	AO	Akira USUI et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy," Jpn. J. Appl. Phys., V. 36, 1997, pp. L899-L902.
	AP	Shigefusa CHICHIBU, "Spatially Resolved Cathodoluminescence Spectra of InGaN Quantum Wells," Appl. Phys. Lett. 71, 1997, pp. 2346-2348.
	AQ	W. W. CHOW et al., "Microscopic Theory of Gain for an InGaN/AlGaN Quantum Well Laser," Appl. Phys. Lett. 71, 1997, pp. 2608-2610.
	AR	A. Atsushi YAMAGUCHI et al., "Optical Recombination Processes in High-Quality GaN Films and InGaN Quantum Wells Grown on Facet-Initiated Epitaxial Lateral Overgrown GaN Substrates," Jpn. J. Apppl. Phys., V. 39, 2000, pp. 2402-2406.
	AS	G. Martin et al., "Valence-Band Discontinuities of Wurtzite GaN, AlN, and InN Heterojunctions Measured by X-Ray Photoemission Spectroscopy," Appl. Phys. Lett. 68, 1996, pp. 2541-2543.
	AT	

EXAMINER	DATE CONSIDERED

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.